Small Signal MOSFET

20 V, 540 mA, Dual N-Channel

Features

- Low R_{DS(on)} Improving System Efficiency
- Low Threshold Voltage
- Small Footprint 1.6 x 1.6 mm
- ESD Protected Gate
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

MAXIMUM RATINGS (T_J = $25^{\circ}C$ unless otherwise noted.)

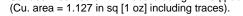
Paramet	Symbol	Value	Unit		
Drain-to-Source Voltage	V _{DSS}	20	V		
Gate-to-Source Voltage			V _{GS}	±7.0	V
Continuous Drain Current	Steady	$T_A = 25^{\circ}C$	1-	540	mA
(Note 1)	State	$T_A = 85^{\circ}C$	ID	390	
Power Dissipation (Note 1)	Stea	dy State	P _D	250	mW
Continuous Drain Current	$t \le 5 s$ $T_A = 25^{\circ}C$		I _D	570	mA
(Note 1)	1 2 3 3	$T_A = 85^{\circ}C$	טי	410	
Power Dissipation (Note 1)	t:	≤ 5 s	P _D	280	mW
Pulsed Drain Current	I _{DM}	1.5	Α		
Operating Junction and Stor	T _J , T _{STG}	–55 to 150	°C		
Source Current (Body Diode)			I _S	350	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			ΤL	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	R_{\thetaJA}	500	°C/W
Junction-to-Ambient – t \leq 5 s (Note 1)		447	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size

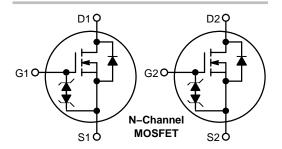


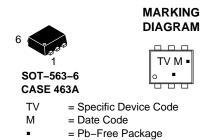


ON Semiconductor®

www.onsemi.com

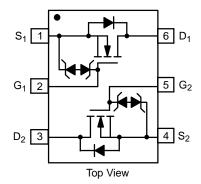
V _{(BR)DSS}	R _{DS(on)} Typ	ID Max (Note 1)
20	400 mΩ @ 4.5 V	
	500 mΩ @ 2.5 V	540 mA
	700 mΩ @ 1.8 V	





(Note: Microdot may be in either location)

PINOUT: SOT-563



ORDERING INFORMATION

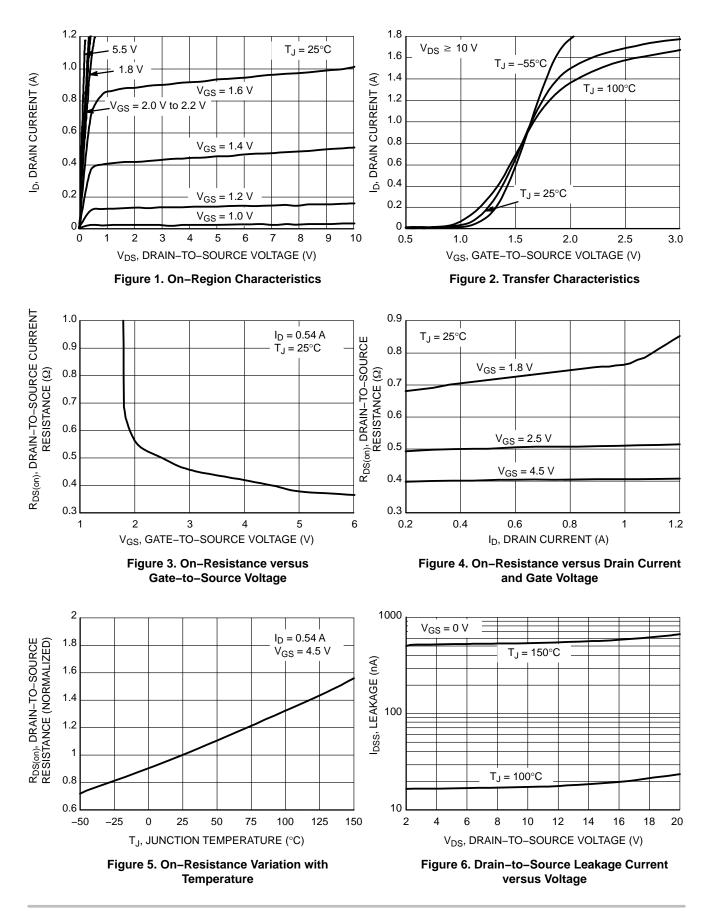
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted.)

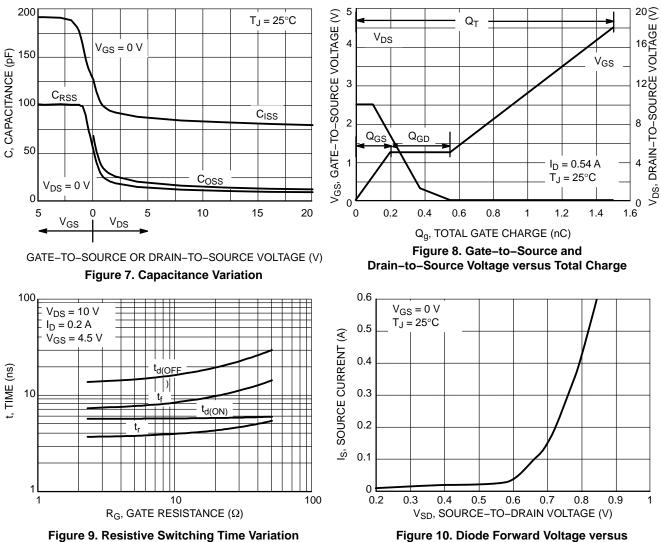
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	-	-		-	-		·
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \text{ V}$	μΑ	20	-	-	V
Drain-to-Source Breakdown Voltage Tem- perature Coefficient	V _{(BR)DSS} /T _J	_	-		14	-	mV/°C
Zero Gate Voltage Drain Current		V _{GS} = 0 V	$T_J = 25^{\circ}C$	-	-	1.0	μΑ
	IDSS	$V_{DS} = 16 V$	$T_J = 125^{\circ}C$	-	-	5.0	
Gate-to-Source Leakage Current	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±4	4.5 V	-	-	± 5.0	μΑ
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_{D} = 250$) μΑ	0.45	-	1.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J	-		-	2.0	-	mV/°C
Drain-to-Source On Resistance		V _{GS} = 4.5 V, I _D = 540 mA		-	0.4	0.55	Ω
	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 500) mA	-	0.5	0.7	-
		V _{GS} = 1.8 V, I _D = 350) mA	-	0.7	0.9	
Forward Transconductance	9 _{FS}	V _{DS} = 10 V, I _D = 540 mA			1.0	-	S
CHARGES AND CAPACITANCES	•						
Input Capacitance	C _{ISS}				80	150	pF
Output Capacitance	C _{OSS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 16 V		-	13	25	
Reverse Transfer Capacitance	C _{RSS}				10	20	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V; I _D = 540 mA		-	1.5	2.5	nC
Threshold Gate Charge	Q _{G(TH)}			-	0.1	-	
Gate-to-Source Charge	Q _{GS}			-	0.2	_	
Gate-to-Drain Charge	Q _{GD}			-	0.35	_	
SWITCHING CHARACTERISTICS, $V_{GS} = V$ (Note 4)						
Turn-On Delay Time	t _{d(ON)}				6.0	_	ns
Rise Time	t _r	V_{GS} = 4.5 V, V_{DD} = 10 V, I_{D} = 540 mA, R_{G} = 10 Ω		_	4.0	-	
Turn–Off Delay Time	t _{d(OFF)}			-	16	-	
Fall Time	t _f	1			8.0	-	
DRAIN-SOURCE DIODE CHARACTERISTIC	s			•	•		<u>. </u>
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 350 mA	$T_J = 25^{\circ}C$	-	0.7	1.2	V
			T _J = 125°C	-	0.6	-	
Reverse Recovery Time	t _{RR}	$V_{GS} = 0 \text{ V}, \text{ d}_{ISD}/\text{d}_t = 100 \text{ A}/\mu\text{s}, \text{ I}_S = 350 \text{ mA}$		_	6.5	_	ns

3. Pulse Test: pulse width $\leq 300 \ \mu$ s, duty cycle $\leq 2\%$. 4. Switching characteristics are independent of operating junction temperatures.

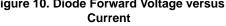
TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)



TYPICAL PERFORMANCE CURVES ($T_J = 25^{\circ}C$ unless otherwise noted)



versus Gate Resistance



ORDERING INFORMATION

Device	Package	Shipping		
NTZD3154NT1G				
NTZD3154NT1H	SOT–563 (Pb–Free)			
NTZD3154NT2G		4000 / Tape & Reel		
NTZD3154NT2H				
NTZD3154NT5G				
NTZD3154NT5H		8000 / Tape & Reel		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

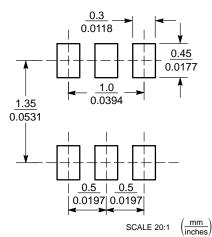
PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A **ISSUE F**

D -X-5 4 O 1 2 b 6 PL е \oplus 0.08 (0.003) 🔘 X | Y NOTES: NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
E	1.10	1.20	1.30	0.043	0.047	0.051	
е	0.5 BSC			0.02 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	1.50	1.60	1.70	0.059	0.062	0.066	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors hamless against all claims, costs, damages, and exponses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

NTZD3154N/D

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: NTZD3154NT1G NTZD3154NT5G